

**30V COMPLEMENTARY ENHANCEMENT MODE MOSFET H-BRIDGE**

**Product Summary**

Device	V <sub>(BR)DSS</sub>	R <sub>Ds(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
N-Channel	30V	25mΩ @ V <sub>GS</sub> = 10V	6.0
		40mΩ @ V <sub>GS</sub> = 4.5V	4.6
P-Channel	-30V	50mΩ @ V <sub>GS</sub> = -10V	-4.2
		80mΩ @ V <sub>GS</sub> = -4.5V	-3.2

**Description**

This new generation complementary MOSFET H-Bridge features low on-resistance achievable with low gate drive.

**Applications**

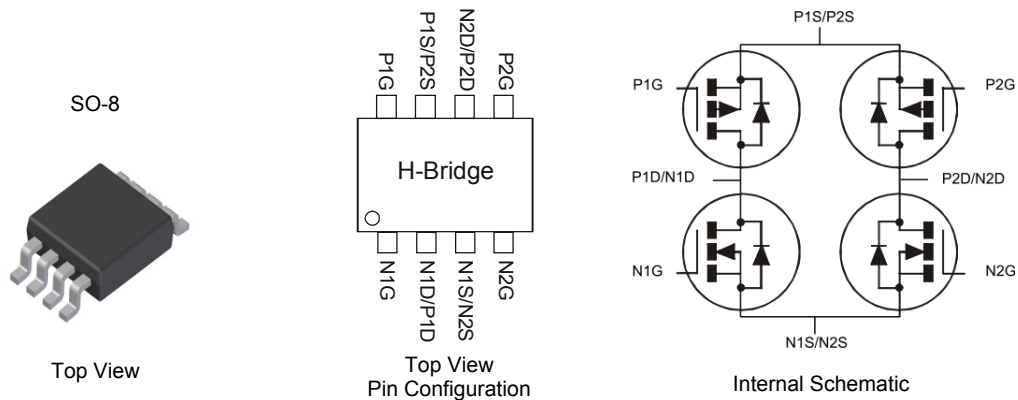
- DC Motor control
- DC-AC Inverters

**Features**

- 2 x N + 2 x P channels in a SOIC package
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.008 grams (approximate)

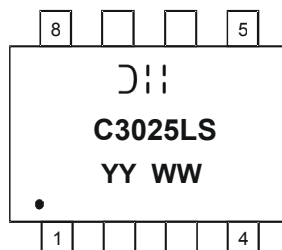


**Ordering Information (Note 4)**

Part Number	Case	Packaging
DMHC3025LSD-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



DII = Manufacturer's Marking  
 C3025LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01 - 53)

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_D$	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	83	$^\circ\text{C/W}$
	$t < 10\text{s}$	50	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	14.5	
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Maximum Ratings N-CHANNEL** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	6.0 4.8	A
	$t < 10\text{s}$ $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	7.8 6.1	A
Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	4.6 3.6	A
	$t < 10\text{s}$ $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	6.1 4.8	A
Maximum Continuous Body Diode Forward Current (Note 5)	$I_S$	2.5	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)	$I_{DM}$	60	A

**Maximum Ratings P-CHANNEL** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 5) $V_{GS} = -10\text{V}$	Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	-4.2 -3.3	A
	$t < 10\text{s}$ $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	-5.4 -4.3	A
Continuous Drain Current (Note 5) $V_{GS} = -4.5\text{V}$	Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	-3.2 -2.5	A
	$t < 10\text{s}$ $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	-4.3 -3.3	A
Maximum Continuous Body Diode Forward Current (Note 5)	$I_S$	-2.5	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)	$I_{DM}$	-30	A

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

**Electrical Characteristics N-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	0.5	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	19	25	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5A
		—	26	40		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A
Forward Transfer Admittance	Y <sub>fs</sub>	—	4	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.70	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	590	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	122	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	58	—		
Gate resistance	R <sub>g</sub>	—	1.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.4	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 7.8A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	11.7	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.1	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	11.2	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 2.4Ω, R <sub>G</sub> = 1Ω,
Turn-On Rise Time	t <sub>r</sub>	—	15	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	17.5	—		
Turn-Off Fall Time	t <sub>f</sub>	—	8.7	—		
Reverse Recovery Time	t <sub>rr</sub>	—	18.3	—	ns	I <sub>F</sub> = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	12	—	nC	

**Electrical Characteristics P-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-0.5	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	43	50	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A
		—	68	80		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
Forward Transfer Admittance	Y <sub>fs</sub>	—	3.5	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -5A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	631	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	137	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	70	—		
Gate resistance	R <sub>g</sub>	—	10.8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.5	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -6A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	11.4	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.4	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	7.5	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>r</sub>	—	4.9	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	28.2	—		
Turn-Off Fall Time	t <sub>f</sub>	—	13.5	—		
Reverse Recovery Time	t <sub>rr</sub>	—	15.1	—	ns	I <sub>F</sub> = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	15.3	—	nC	

Notes: 6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

**Typical Characteristics - N-CHANNEL**

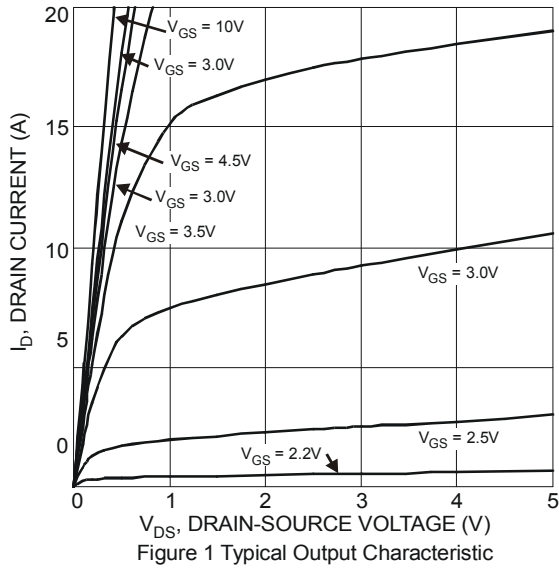


Figure 1 Typical Output Characteristic

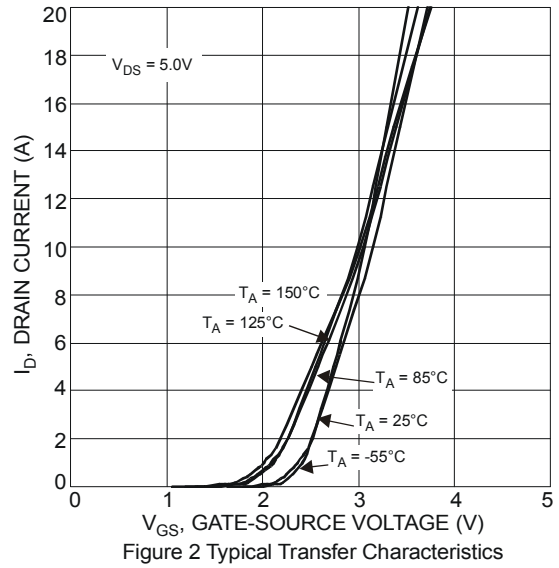


Figure 2 Typical Transfer Characteristics

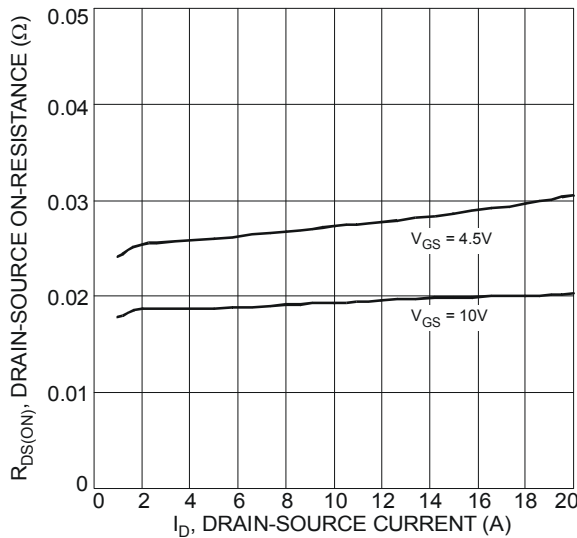


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

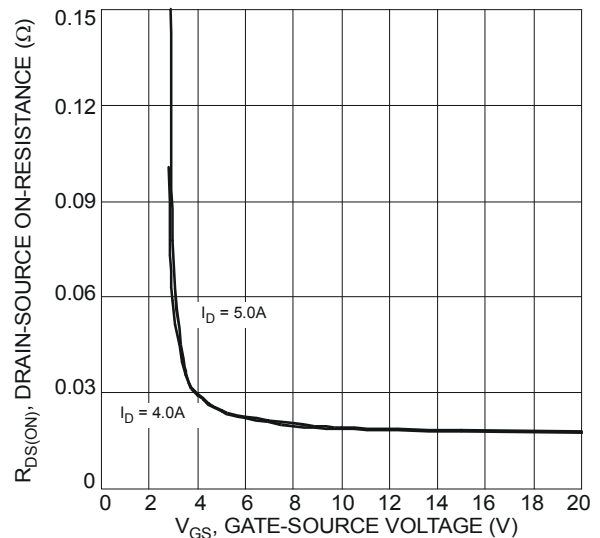


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

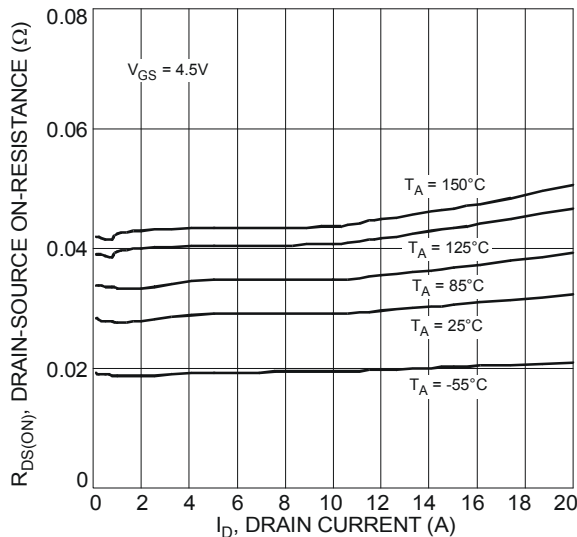


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

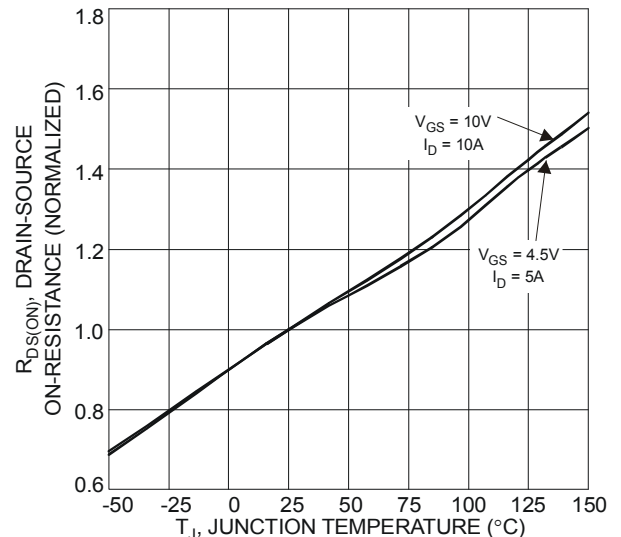


Figure 6 On-Resistance Variation with Temperature

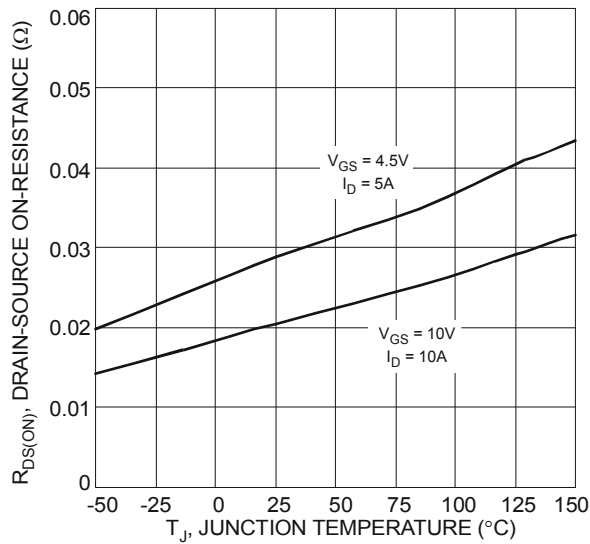


Figure 7 On-Resistance Variation with Temperature

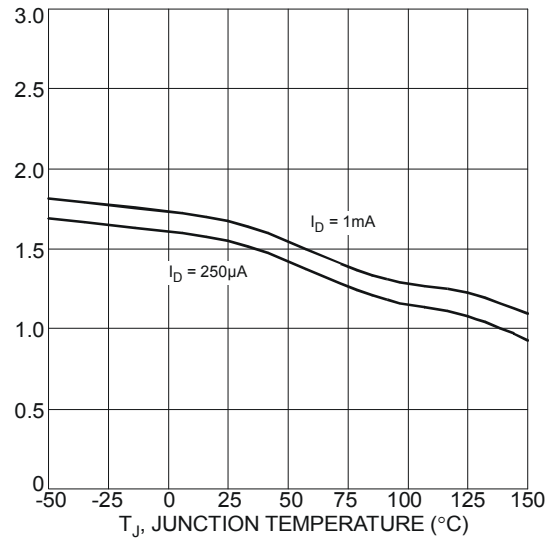


Figure 8 Gate Threshold Variation vs. Ambient Temperature

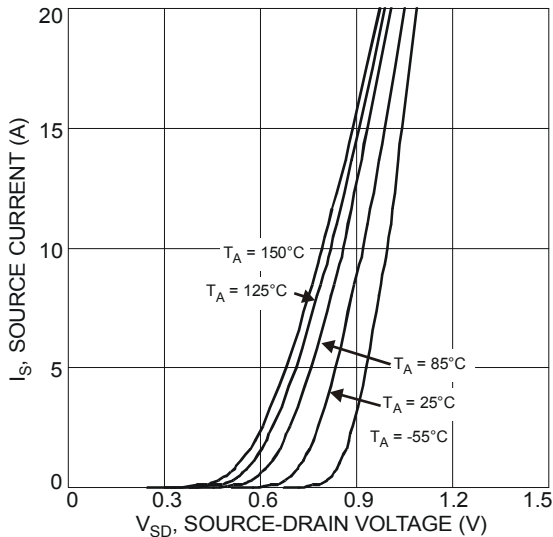


Figure 9 Diode Forward Voltage vs. Current

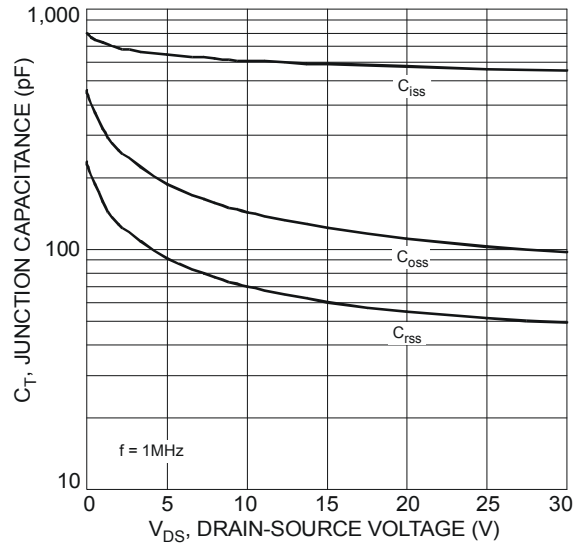


Figure 10 Typical Junction Capacitance

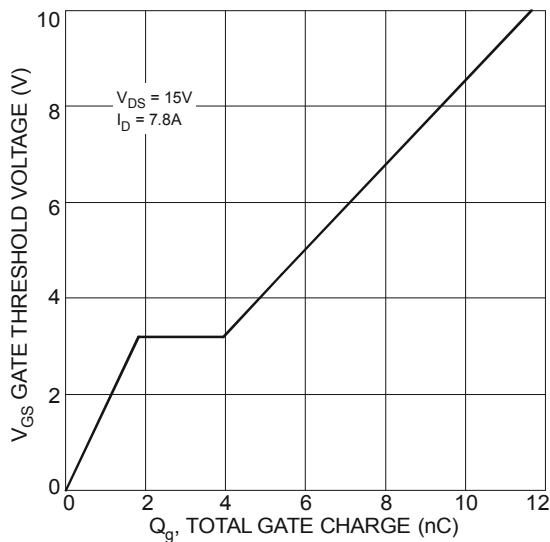
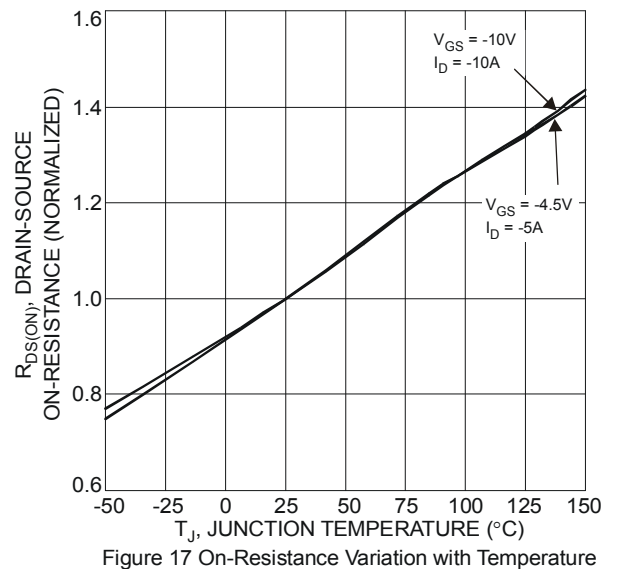
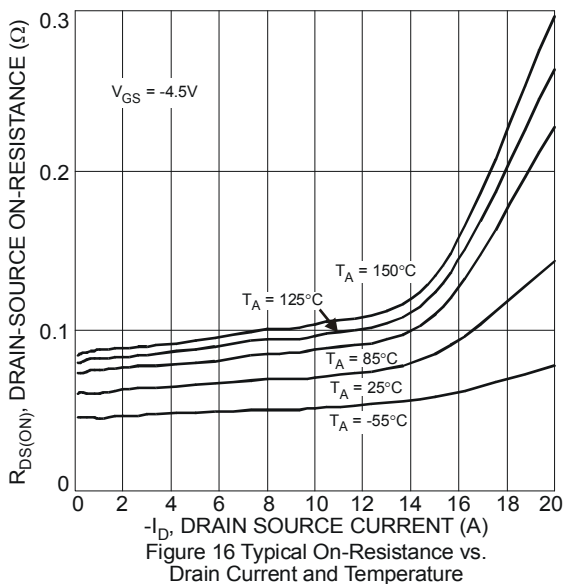
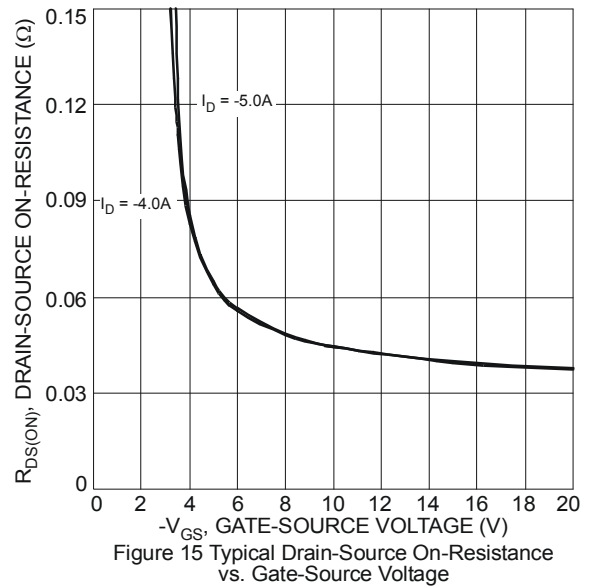
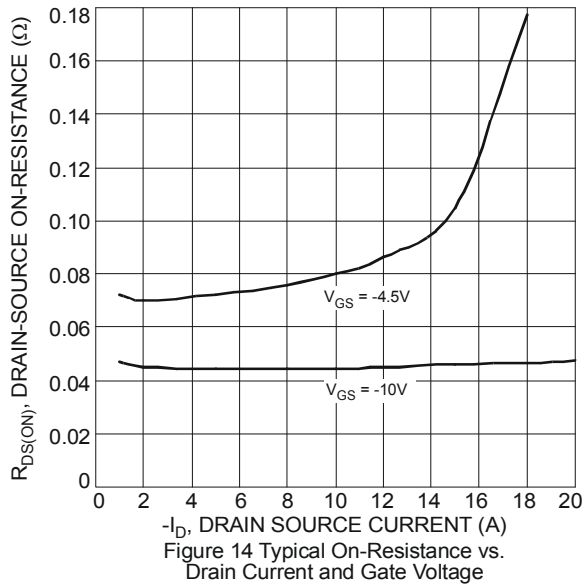
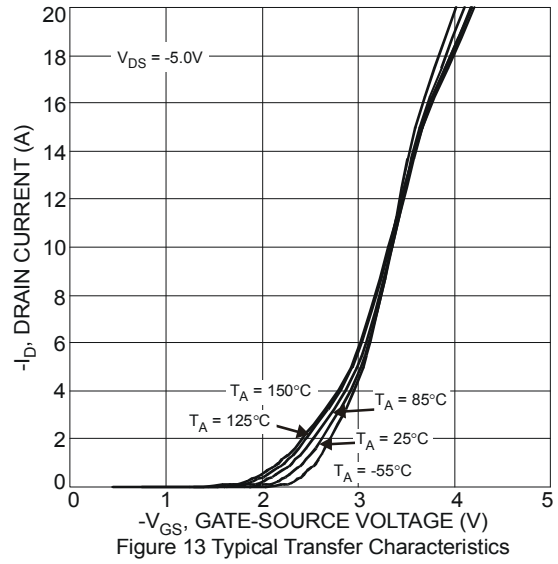
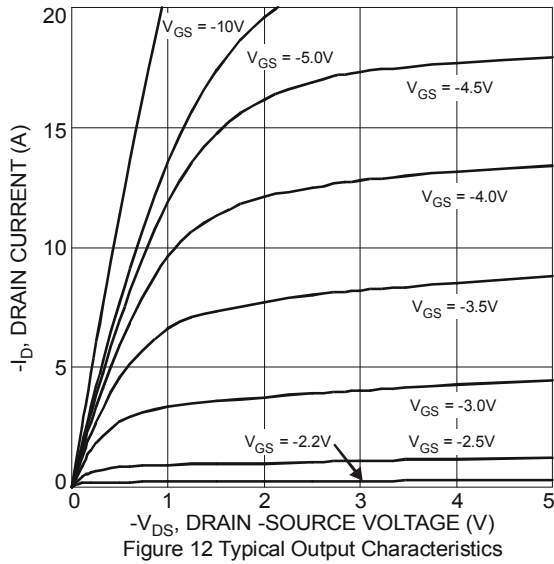


Figure 11 Gate Charge

**Typical Characteristics - P-CHANNEL**



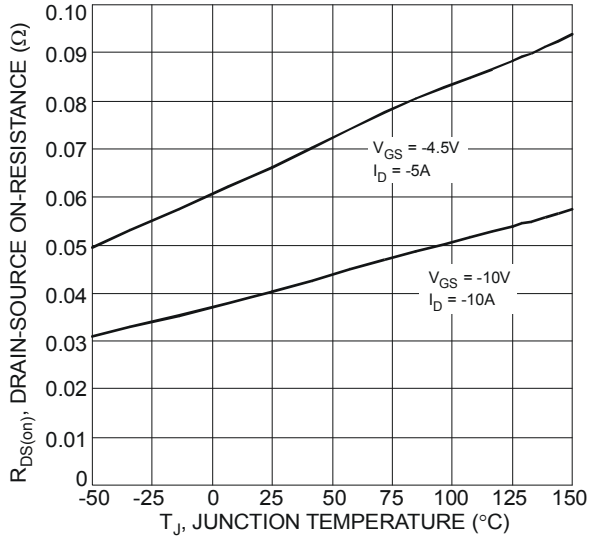


Figure 18 On-Resistance Variation with Temperature

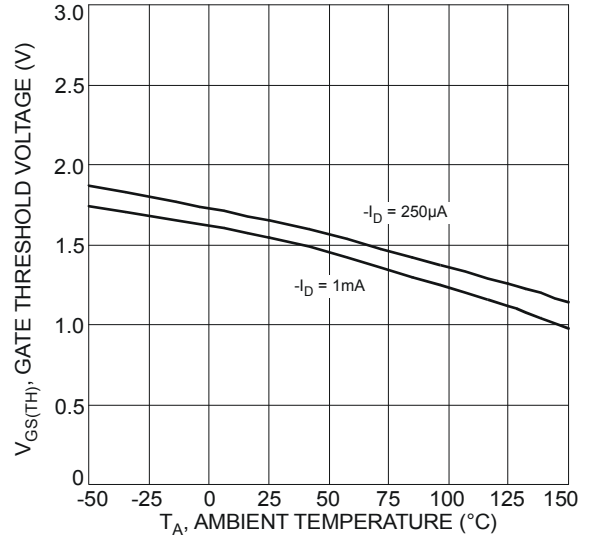


Figure 19 Gate Threshold Variation vs. Ambient Temperature

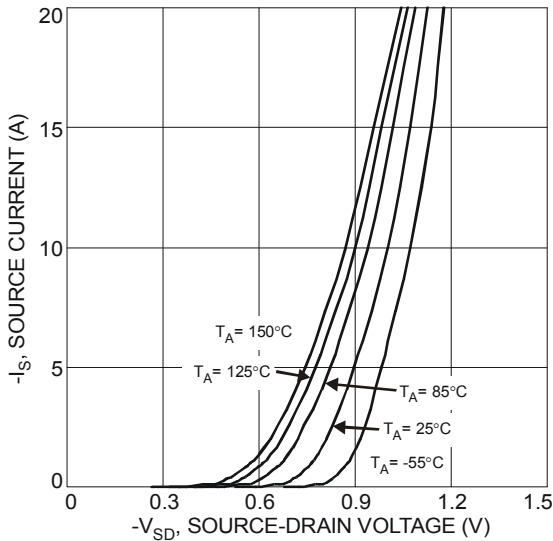


Figure 20 Diode Forward Voltage vs. Current

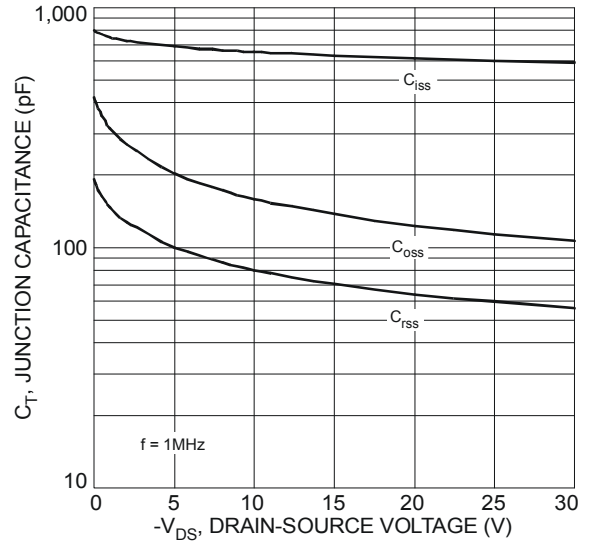


Figure 21 Typical Junction Capacitance

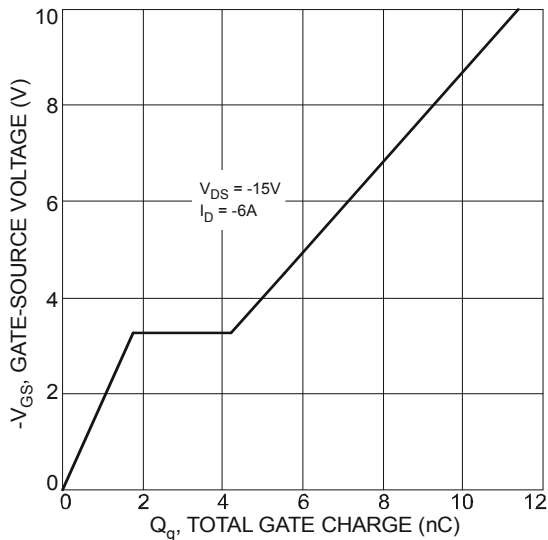
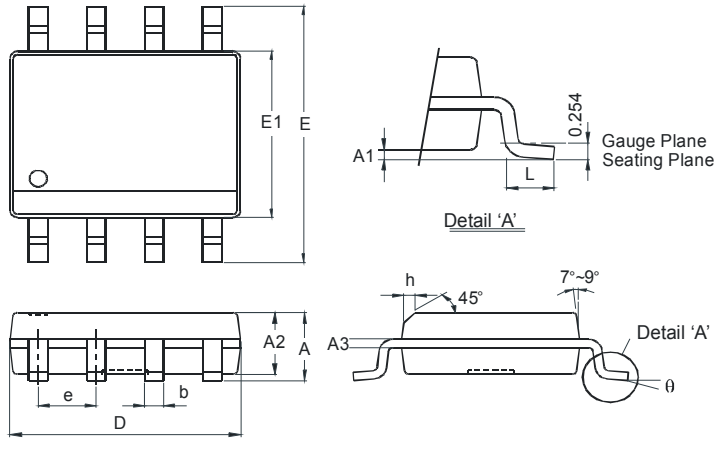


Figure 22 Gate-Charge Characteristics

**Package Outline Dimensions**

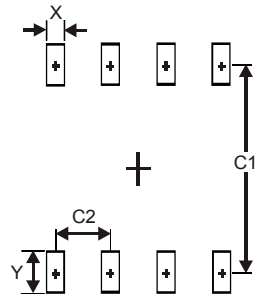
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



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